

## Silicon NPN Phototransistor

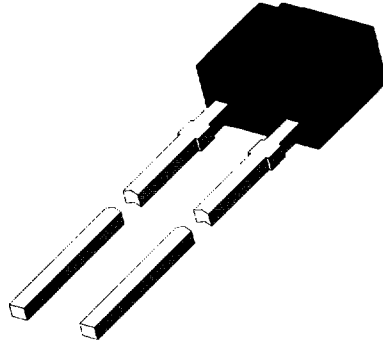
### Description

TEST2600 is a high sensitive silicon NPN epitaxial planar phototransistor in a miniature side view plastic package with cylindrical lens.

Its epoxy casting is designed as a infrared filter to spectrally match to GaAs IR emitters ( $\lambda_p=950\text{nm}$ ).

### Features

- High radiant sensitivity (2.5 mA)
- Miniature side view package with cylindrical lens
- Very wide viewing angle  $\phi = \pm 30^\circ / \pm 60^\circ$
- Suitable for near IR radiation
- Matches with TSSS 2600 IR emitter



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### Applications

Optical switches  
Counters and sorters  
Interrupters  
Tape and card readers  
Encoders  
Position sensors

### Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Collector Emitter Voltage		$V_{\text{CEO}}$	70	V
Emitter Collector Voltage		$V_{\text{ECO}}$	5	V
Collector Current		$I_{\text{C}}$	50	mA
Peak Collector Current	$t_p/T = 0.5, t_p \leq 10 \text{ ms}$	$I_{\text{CM}}$	100	mA
Total Power Dissipation	$T_{\text{amb}} \leq 55^\circ\text{C}$	$P_{\text{tot}}$	100	mW
Junction Temperature		$T_{\text{J}}$	100	$^\circ\text{C}$
Storage Temperature Range		$T_{\text{stg}}$	-55...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 3 \text{ s}, 2 \text{ mm from case}$	$T_{\text{sd}}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{\text{thJA}}$	450	K/W

## Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	$I_C = 1\text{ mA}$	$V_{(BR)CEO}$	70			V
Collector Dark Current	$V_{CE} = 20\text{ V}, E = 0$	$I_{CEO}$		1	100	nA
Collector Emitter Capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}, E=0$	$C_{CEO}$		6		pF
Collector Light Current	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, V_{CE}=5\text{ V}$	$I_{ca}$	1	2.5		mA
Angle of Half Sensitivity	horizontal	$\phi_1$		$\pm 30$		deg
	vertical	$\phi_2$		$\pm 60$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		920		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		850..980		nm
Collector Emitter Saturation Voltage	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, I_C=0.1\text{ mA}$	$V_{CEsat}$			0.3	V
Turn-On Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{on}$		6		$\mu\text{s}$
Turn-Off Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{off}$		5		$\mu\text{s}$
Cut-Off Frequency	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$f_c$		110		kHz

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

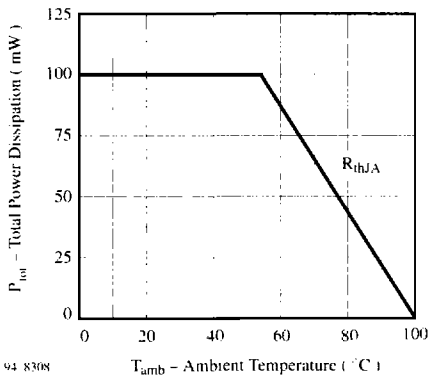


Figure 1. Total Power Dissipation vs. Ambient Temperature

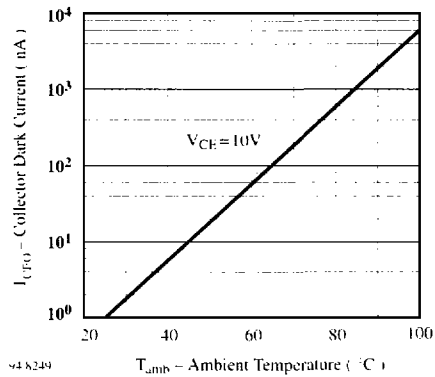


Figure 2. Collector Dark Current vs. Ambient Temperature

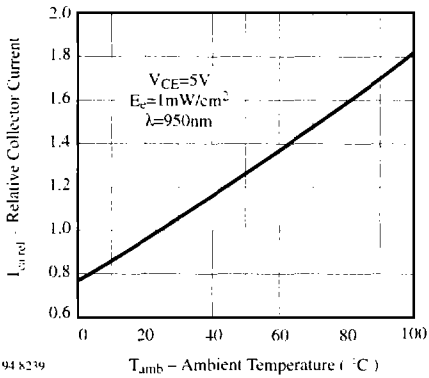


Figure 3. Relative Collector Current vs. Ambient Temperature

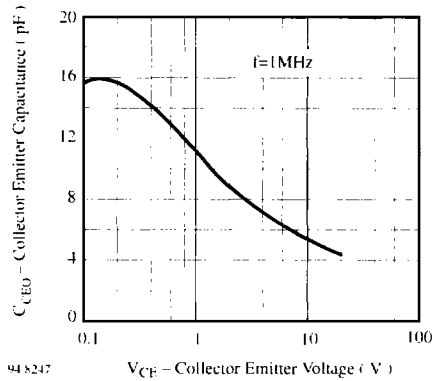


Figure 6. Collector Emitter Capacitance vs. Collector Emitter Voltage

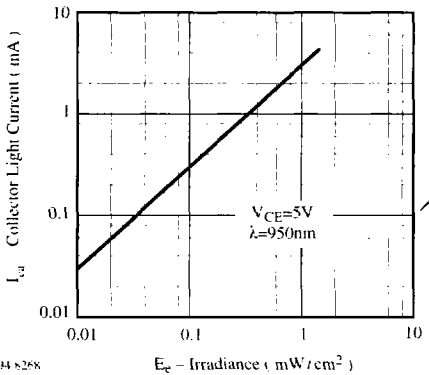


Figure 4. Collector Light Current vs. Irradiance

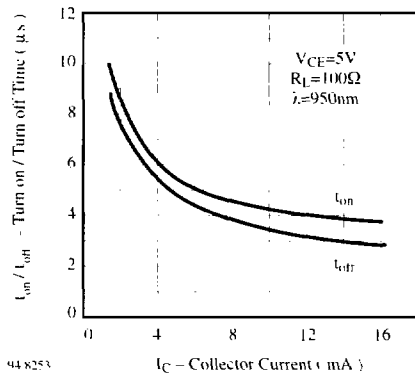


Figure 7. Turn On/Turn Off Time vs. Collector Current

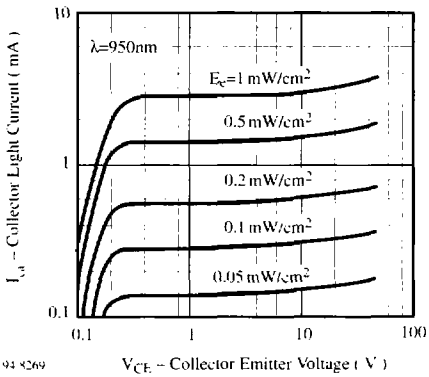


Figure 5. Collector Light Current vs. Collector Emitter Voltage

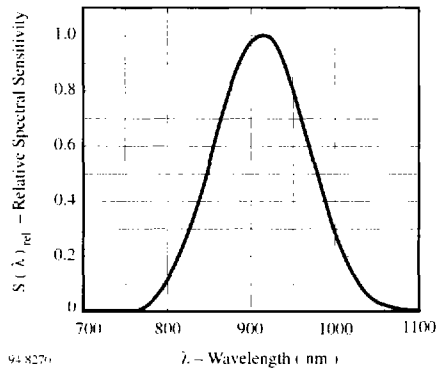
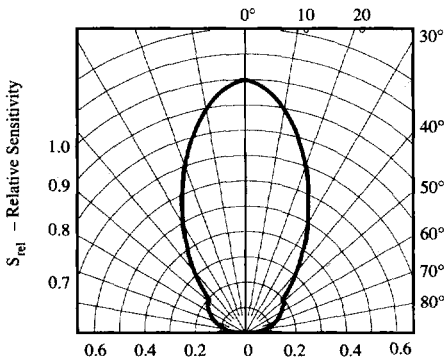
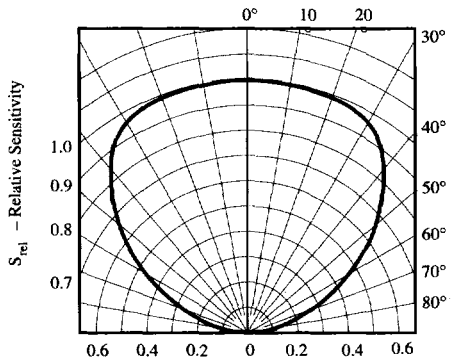


Figure 8. Relative Spectral Sensitivity vs. Wavelength



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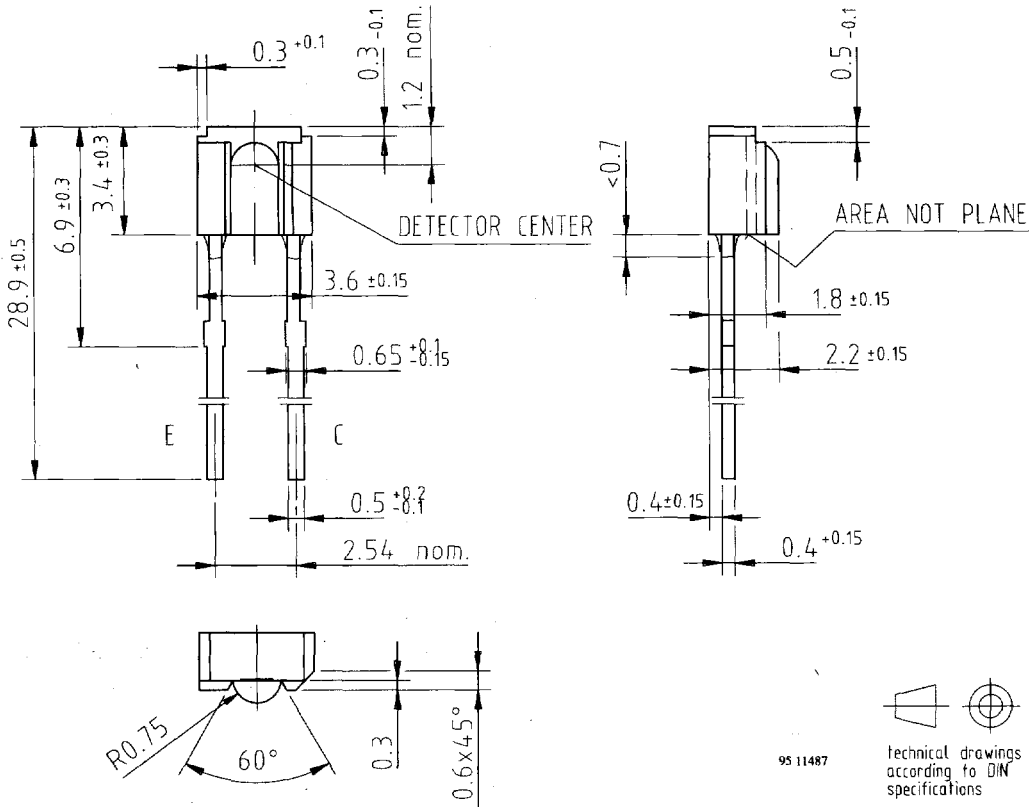
Figure 9. Relative Radiant Sensitivity vs. Angular Displacement



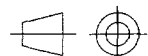
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Figure 10. Relative Radiant Sensitivity vs. Angular Displacement

## Dimensions in mm



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technical drawings  
according to DIN  
specifications